Abstract

SEMICONDUCTOR DEVICE AND METHOD OF FORMING RDL OVER CONTACT PAD WITH HIGH ALIGNMENT TOLERANCE OR REDUCED INTERCONNECT PITCH

A semiconductor device has a semiconductor die with an active surface. A first conductive layer is formed over the active surface. A first insulating layer is formed over the active surface. A second insulating layer is formed over the first insulating layer and first conductive layer. A portion of the second insulating layer is removed over the first conductive layer so that no portion of the second insulating layer overlies the first conductive layer. A second conductive layer is formed over the first conductive layer and first and second insulating layers. The second conductive layer extends over the first conductive layer up to the first insulating layer. Alternatively, the second conductive layer extends across the first conductive layer up to the first insulating layer on opposite sides of the first conductive layer. A third insulating layer is formed over the second conductive layer and first and second insulating layers.
(Fig. 5a)